

10/520439

PCT/G13/2002 02875

05 JAN 2005



REC'D 28 JUL 2002	10/520439 PCT/PTO
WIPO	PCT

INVESTOR IN PEOPLE

The Patent Office

Concept House

Cardiff Road

Newport

South Wales

NP10 8QQ

**PRIORITY
DOCUMENT**

SUBMITTED OR TRANSMITTED IN
COMPLIANCE WITH RULE 17.1(a) OR (b)

I, the undersigned, being an officer duly authorised in accordance with Section 74(1) and (4) of the Deregulation & Contracting Out Act 1994, to sign and issue certificates on behalf of the Comptroller-General, hereby certify that annexed hereto is a true copy of the documents as originally filed in connection with the patent application identified therein.

I also certify that the attached copy of the request for grant of a Patent (Form 1/77) bears an amendment, effected by this office, following a request by the applicant and agreed to by the Comptroller-General.

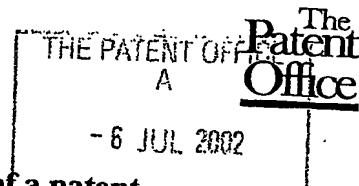
In accordance with the Patents (Companies Re-registration) Rules 1982, if a company named in this certificate and any accompanying documents has re-registered under the Companies Act 1980 with the same name as that with which it was registered immediately before re-registration save for the substitution as, or inclusion as, the last part of the name of the words "public limited company" or their equivalents in Welsh, references to the name of the company in this certificate and any accompanying documents shall be treated as references to the name with which it is so re-registered.

In accordance with the rules, the words "public limited company" may be replaced by p.l.c., plc, P.L.C. or PLC.

Re-registration under the Companies Act does not constitute a new legal entity but merely subjects the company to certain additional company law rules.

Signed

Dated 14 July 2003



1 / 77 77
08 JUL 02 E731652-2 D10007
P01/7700 0.00-0215736.0

Request for grant of a patent

(See the notes on the back of this form. You can also get an explanatory leaflet from the Patent Office to help you fill in this form)

1. Your reference

P3093 GB PRO

The Patent Office

Cardiff Road
Newport
South Wales
NP9 1RH

- 6 JUL 2002

2. Patent application number
(The Patent Office will fill in this part)

0215736.0

3. Full name, address and postcode of the or of each applicant *(underline all surnames)*

AOTI OPERATING COMPANY, INC.
131 NW HAWTHORNE AVENUE
SUITE 207
BEND, OREGON 97701, US

Patents ADP number *(if you know it)*

8113805002

If the applicant is a corporate body, give the country/state of its incorporation

DELAWARE, USA

L+ 24/7/02

4. Title of the invention

MONITORING APPARATUS AND METHOD FOR
IMPROVING THE ACCURACY AND REPEATABILITY OF
ELECTROCHEMICAL CAPACITANCE VOLTAGE (ECV)
MEASUREMENTS

5. Name of your agent *(if you have one)*

NOVAGRAAF PATENTS LIMITED

"Address for service" in the United Kingdom to which all correspondence should be sent *(including the postcode)*

THE CRESCENT
54 BLOSSOM STREET
YORK YO14 1AP

Patents ADP number *(if you know it)*

-07296486002 8299166001

6. If you are declaring priority from one or more earlier patent applications, give the country and the date of filing of the or of each of these earlier applications and <i>if you know it</i> the or each application number	Country	Priority application number <i>(if you know it)</i>	Date of filing <i>(day / month / year)</i>

7. If this application is divided or otherwise derived from an earlier UK application, give the number and the filing date of the earlier application	Number of earlier application	Date of filing <i>(day / month / year)</i>

8. Is a statement of inventorship and of right to grant of a patent required in support of this request? <i>(Answer 'Yes' if</i>		
	a) any applicant named in part 3 is not an Inventor, or b) there is an Inventor who is not named as an applicant, or c) any named applicant is a corporate body. <i>See note (d))</i>	YES

Patents Form 1/77

9. Enter the number of sheets for any of the following items you are filing with this form.
Do not count copies of the same document

Continuation sheets of this form

Description	14 /
Claim(s)	6 / CF
Abstract	1 /

Drawing(s) 4 + 4

10. If you are also filing any of the following, state how many against each item.

Priority documents

Translations of priority documents

Statement of inventorship and right
to grant of a patent (Patents Form 7/77)

Request for preliminary examination
and search (Patents Form 9/77)

Request for substantive examination
(Patents Form 10/77)

Any other documents
(please specify)

11.

I/We request the grant of a patent on the basis of this application.

Signature  Date 05/07/2002
NOVAGRAAF PATENTS LIMITED

12. Name and daytime telephone number of PETER WILSON (DR)
person to contact in the United Kingdom

01904 610586

Warning

After an application for a patent has been filed, the Comptroller of the Patent Office will consider whether publication or communication of the invention should be prohibited or restricted under Section 22 of the Patents Act 1977. You will be informed if it is necessary to prohibit or restrict your invention in this way. Furthermore, if you live in the United Kingdom, Section 23 of the Patents Act 1977 stops you from applying for a patent abroad without first getting written permission from the Patent Office unless an application has been filed at least 6 weeks beforehand in the United Kingdom for a patent for the same invention and either no direction prohibiting publication or communication has been given, or any such direction has been revoked.

Notes

- a) If you need help to fill in this form or you have any questions, please contact the Patent Office on 0645 500505.
- b) Write your answers in capital letters using black ink or you may type them.
- c) If there is not enough space for all the relevant details on any part of this form, please continue on a separate sheet of paper and write "see continuation sheet" in the relevant part(s). Any continuation sheet should be attached to this form.
- d) If you have answered 'Yes' Patents Form 7/77 will need to be filed.
- e) Once you have filled in the form you must remember to sign and date it.
- f) For details of the fee and ways to pay please contact the Patent Office.

**MONITORING APPARATUS AND METHOD FOR IMPROVING THE
ACCURACY AND REPEATABILITY OF ELECTROCHEMICAL
CAPACITANCE VOLTAGE (ECV) MEASUREMENTS**

5

The invention relates to an apparatus and method for improving the accuracy of Electrochemical Capacitance Voltage (ECV) profiling measurements by alerting the operator to the presence of surface films or gas bubbles during the etching process and by determining the true measurement area at the end of 10 the measurement cycle and using the new value to recalculate the carrier concentration data. By making the area measurement integral to the ECV tool, every sample measurement can be corrected for the true measurement area, leading to improved accuracy and eliminating a large source of error. Further reduction in error is achieved by using the integral measurement system to 15 monitor the sample surface during measurement for surface films and gas bubbles.

Semiconductor devices are made by sandwiching layers of material of different electrical and/or optical properties together. The layers are formed by 20 epitaxial growth on or ion implantation or diffusion into a substrate wafer. Correct device operation necessitates close control of layer properties including carrier concentration and thickness. U.S. Pat. Nos. 4,028,207 & 4,168,212 describe the ECV profiling method, which is used for determining the carrier concentration as a function of depth into the layer and is therefore 25 ideally suited to measuring these parameters.

ECV profiling makes use of the diode structure formed when a conducting liquid (electrolyte) is placed in contact with a semiconductor. The capacitance of the junction, in the reverse bias region, is determined by the magnitude of

the applied bias and the carrier concentration vs. depth profile. By measuring this capacitance as a function of bias the carrier concentration depth profile can be determined. In this mode of operation the ECV profiler is similar to tools, which use metallisation or mercury in place of an electrolyte to form a diode structure. However, such tools are usually restricted to shallow depth profiles due to reverse bias breakdown of the semiconductor-metal junction. By using an electrolyte this limitation is overcome. The electrolyte is used to electrochemically etch into the sample, increasing the depth profiled without increasing the measurement bias. This makes ECV profiling a very powerful method for characterizing multi-layer structures.

Some of the factors which affect the accuracy and reproducibility of ECV profiling have been mentioned in "I. Mayes - Accuracy and Reproducibility of the Electrochemical Profiler, Mat Sci & Eng B80 (2001) 160-163". This paper concludes that with 'best practice' the reproducibility of the method can be reduced to a standard deviation of around 2%. However, without careful control of the measurement a standard deviation of around 8% is more typical.

Usually a plastic ring, referred to as a sealing ring, defines the area of contact between the electrolyte and the semiconductor sample. Wear and distortion of this ring have a significant effect on the reproducibility of the contact area. In addition the contact pressure and wetting characteristics of the electrolyte have to be considered. All these factors influence the accuracy of the measurement.

Accurate measurements depend on knowing the precise area of contact between the test sample and the electrolyte and ensuring that it remains stable throughout the measurement process. As the carrier concentration, determined by this method, is inversely proportional to the area squared and the depth profiled is inversely proportional to area, large errors can occur. A 10% error

in the contact area results in a 10% error in depth and more importantly a 20% error in the calculated carrier concentration. Although not all of the error can be corrected by measuring the final etch well area, routine measurement of this after each run significantly improves the repeatability of the measurement.

5

Gas bubbles and surface films can affect the measurement during profiling. Gas bubbles arise due to trapped air when the electrochemical cell is initially filled, or during electrolyte circulation or are a result of the electrochemical reactions used to etch the sample. Surface films arise from non-ideal 10 electrochemical etching and are usually prevented by selecting a more appropriate electrolyte. Both gas bubbles and surface films lead to non-planer etching which changes the measurement area and can seriously affect measurement quality when multi-layer structures or structures with changing carrier concentration are being profiled. Gas bubbles can be removed by 15 controlling the electrolyte flow and surface films can be prevented by careful control of the etching conditions. The etching bias, current and electrolyte flow rate are variables that can be controlled to alleviate these problems. Often the operator is not aware of the presence of gas bubbles or surface films and does not take action until their effect is seen in the electrical measurements, by 20 which time the accuracy of the measurement is poor.

It is common practice to routinely check the sealing ring area by using an anodized n-type GaAs substrate, referred to as a 'blue film slice'. The 'blue film slice' is profiled to form a shallow etch well, typically less than 0.5 25 microns deep. The slice is then removed from the tool and the area of the etched well is determined using a measuring microscope or some form of camera based metrology system. It is not the purpose of this invention to eliminate the need for this measurement as it provides important addition

information on the quality of the seal and can be made without removing the sample from the tool using the apparatus described herein.

Electrochemically etching occurs when the sample is the anode (biased

5 positively with respect to a counter electrode). For p-type material this is the forward bias condition and electrochemical etching readily takes place. For n-type material this is the reverse bias condition and electrochemical etching only occurs when the sample is illuminated with light of energy above the band-gap of the material.

10

Seepage under the edge of the ring means that the illuminated area is smaller than the area of contact between the sample and the electrolyte. This difference is important as the capacitance measurement is made over the whole of the sample area in contact with the liquid. The 'blue film slice' is
15 used to measure the difference in these two areas. This excess area, A_{excess} , increases as the seal wears and is defined as:

$$A_{excess} = A_{wetted} - A_{illum}$$

20 Where A_{wetted} is the contact area between the electrolyte and the sample (wetted area) and A_{illum} is the area illuminated by light, which for n-type material is the area profiled during the electrochemical etching process. The excess area is a small ring of material that lies under or close to the sealing ring edge. The capacitance associated with this ring of material gives rise to errors, especially
25 for samples with a highly doped surface layer and lower doped interior, referred to as 'Hi-Lo' structures.

In addition to 'blue film slice' calibrations, some users measure the area of the etched well when the measurement is complete. The area of the sidewall is

generally ignored, as the depth of the etched well is usually small in comparison with its diameter. Occasionally, the sample is also stylus profiled to check for roughness and to see that the etched well is planer. These measurements are made using other instruments such as a measuring microscope and a stylus profiler, which are not part of the ECV profiling tool.

5 As a result these measurements are not always made and this leads to poor reproducibility. Further, without some means of viewing the sample surface during the measurement the conditions that lead to roughness and non-planer etching are difficult to avoid.

10

It is an object of the invention to mitigate some or all of these disadvantages and so improve accuracy and reproducibility of ECV profile measurements.

It is a particular object of the invention to provide a method of ECV profiling

15 which allows for viewing of the sample during electrolyte filling and ECV profiling and for viewing and measuring the etched well area, without the need to remove the sample from the apparatus.

It is a particular object of the invention to provide a method of ECV profiling

20 which provides valuable information to the user to optimize the conditions, to alleviate problems with gas bubbles and surface films and to improve the accuracy and repeatability of the measurement.

Thus, in accordance with the invention in a first aspect, an in-situ method for

25 improving the accuracy and repeatability of Electrochemical Capacitance Voltage (ECV) profiling comprises the steps of:

providing a sample, a means of defining a measurement region on the sample, an electrochemical cell to contain the electrolyte which is in contact with the sample, and ECV profiling in conventional manner;

monitoring the sample during the electrolyte fill cycle to observe and obtain measurements of the presence of gas bubbles and surface films formed thereon;

monitoring the etched well during profiling;

5 measuring the etched well area at the end of the profile;

applying the said measurements to the raw profiling data to produce adjusted data more reproducibly representative of the ECV profile.

In accordance with the method a suitable optical system is used which can be
10 combined with the ECV profiling apparatus to both monitor the etched well during the measurement and accurately measure the well area once the measurement is complete, without removing the sample from the apparatus. This results in both improved accuracy and reproducibility and saves wasting time on measurements that may have been made under non-ideal conditions.

15 In a particular embodiment of the method, observation and measurement of the etched well comprises the use of a light source, preferably of energy above the band-gap of the sample, to illuminate the sample, and the use of image collection means to collect a reflected light image from the sample and image
20 analysis means to analyse the reflected light image from the sample and obtain the said measurements from the etched well.

The image collection means preferably comprises digital imaging means and/or incorporates means to digitise the image for subsequent analysis by the
25 image analyser. For example the imaging means comprises a CCD camera.

Preferably, the reflected light image is directed towards the imaging means by use of suitable directing means such as a beam splitter.

The light source has a dual purpose, providing light for etching n-type semiconductors and light for viewing the bottom of the etched well. A second light source of energy below the band-gap of the sample may be provided to illuminate the sample during electrical measurements.

5

In a preferred embodiment the same light source and imaging means are used to view and monitor the sample during the electrolyte fill cycle and the etched well area subsequently. In this embodiment the method comprises using the light source to generate a reflected light image of the sample during the 10 electrolyte fill cycle and collecting the image via the imaging means, draining the electrochemical cell, taking the cell out of the optic path, using the light source to generate a reflected light image of the etched well area collecting the image via the imaging means to measure the said area.

15 In accordance with the invention in a second aspect, an apparatus for improving the accuracy and repeatability of Electrochemical Capacitance Voltage (ECV) profiling comprises means to monitor a sample during the electrolyte fill cycle to observe and obtain measurements of the presence of gas bubbles and surface films formed thereon, means to monitor the etched 20 well during profiling, means to obtain a measurement of the etched well area at the end of the profile, whereby the said measurements may applied to raw profiling data to produce adjusted data more reproducibly representative of the ECV profile.

25 Preferably, a suitable optical system is provided to obtain the said measurements. In particular, a single optical system is adapted for use in combination with the ECV profiling apparatus to both monitor the etched well during the measurement and accurately measure the well area once the measurement is complete, without removing the sample from the apparatus.

In a preferred embodiment, the means to monitor a sample during the electrolyte fill cycle, the means to monitor the etched well during profiling, and the means to obtain a measurement of the etched well comprises a single
5 optical system, preferably including a light source, preferably of energy above the band-gap of the sample, to illuminate the sample, and image collection means to collect a reflected light image from the sample, and further preferably including image analysis means to analyse the reflected light image from the sample and obtain the said measurements.

10

Thus, in accordance with the invention in-situ apparatus is provided with a single optical system for monitoring gas bubbles and surface films during the etching process and for measuring the etched well area at the end of the measurement cycle comprising:

15

Conveniently, for materials with a band-gap less than 2.5eV, the light source is a quartz halogen lamp. However it is within the scope of the invention to use other light sources, such as a UV discharge lamp for wider band-gap materials.

20

The image collection means preferably comprises digital imaging means and/or incorporates means to digitise the image for subsequent analysis by the image analyser. For example the imaging means comprises a CCD camera.

25

The analysing means conveniently comprise a suitable programmed computer. The imaging means is preferably interfaced to a computer to pass a digitized image thereto for processing the said measurements and/or applying the measurements to raw profiling data in the manner of the invention using suitable analysis software.

The data from the image is processed using software that can extract the etched well area and in the case of a suitable sample such as a 'blue film slice' is able to differentiate between the wetted and illuminated areas, measure them
5 and determine the excess area.

Additionally or alternatively data from the image is processed using software to analyse the image and use the results of the analysis to provide automatic feedback for elimination of gas bubbles and surface films.

10

Additionally or alternatively the software may control variable magnification on the imaging means.

Preferably, the reflected light image is directed towards the imaging means by
15 use of suitable directing means such as a beam splitter.

In a preferred embodiment the same light source and imaging means are used to view and monitor the sample during the electrolyte fill cycle and the etched well area subsequently. Conveniently, the apparatus further includes means to
20 receive an electrochemical cell in the optical path of the imaging means during the electrolyte fill cycle, which are adapted to enable the cell to be removed from the optical path subsequently, so the same light source may be used to generate a reflected light image of the etched well area collecting the image via the imaging means to measure the said area.

25

A mechanism for removing the electrochemical cell from the optical path so that the camera can view the etched well and surrounding material without interference from the cell and any sealing ring etc is conveniently provided.

Focussing means may be provided to compensate for the difference in focal length when the cell windows and electrolyte are in the path. A variable focus camera or like imaging means may be provided. More simply, a fixed focus camera or like imaging means may be provided, and a removable lens in the

5 light path to the imaging means may be provided to compensate for the difference in focal length. A mechanism may be provided for moving the sample along the optical axis so that it focuses on the fixed focus camera or like imaging means.

10 The electrochemical cell may be provided with a window for viewing and illuminating the sample, which is preferably slightly angled to prevent reflection from the surfaces of the window degrading the reflected image on the camera or other imaging means.

15 The apparatus may further comprise a flip lens before the camera or other imaging means to correct for refraction by the electrolyte and cell window when the apparatus is being used to view and/or monitor gas bubbles and surface films

20 The apparatus is preferably interfaced to a suitable computer, and conveniently the computer controlling the ECV profiling measurement, so that the image of the etched well can be viewed in real time together with the electrical measurements.

25 An embodiment of the invention will now be described, by way of example only, with reference to the following Figure's wherein:

Referring to the figures and firstly to **Figure 1** there is shown a diagrammatic illustration of an apparatus in accordance with the invention.

The apparatus essentially comprises a camera viewing system which, towards the left hand side, comprises a *light source* [1-6], towards the left hand side, comprises the *sample* [17], *sealing ring* [16], *electrochemical cell* [19] and a means [20] of moving the ring and electrochemical cell out of the optical path, towards the top, comprises a *camera* [23] for viewing the sample and in the centre of the figure there are shown various optical components for directing light through the system.

10 In the embodiment shown in **Figure 1**, a quartz halogen *lamp* [1] and *optical filter* [4] are used to provide the light of energy above the band-gap of the sample for etching the sample and for viewing the etched well.

15 The light from *lamp* [1] is collimated by the *condenser* [2] before passing through a *heat filter* [3] *short-pass or band-pass filter* [4] *field lens* [5] and *aperture* [6]. The light then passes a *shutter* [7], which is operated by a *solenoid* [8] in order to control the period of time the sample is etched for. A *fold mirror* [9] reflects the beam to an *imaging lens* [10], which re-images the *aperture* [6] at the *sample* position [17].

20 The beam from the *imaging lens* [10] passes through a *beamsplitter* [11] *vapour barrier window* [12] in the *vapour barrier* [13] *cell rear window* [14] *electrolyte* [15] to the *sealing ring* [16] abutting the *sample* [17] located by the *sample holder* [18]. The *vapour barrier window* [12] and *cell rear window* [14] are inclined at a slight angle to prevent reflections from their surfaces from entering the field of view of the *camera* [23].

The etch process can be monitored by the *camera* [23] through the *lens* [22] and the *supplementary lens* [21] by means of reflection from the rear face of

the beamsplitter [11R]. The *beamsplitter* [11] is made with sufficient thickness to prevent reflections from the interior of the front face [11F] entering the field of view of the camera; reflections from the exterior of the front face [11F] are absorbed by means of a *non-reflective surface* [24], see
5 **Figure 2.** The *supplementary lens* [21] compensates for the refractive index changes [in the light path] of the *cell rear window* [14] and *electrolyte* [15].

In the absence of gas bubbles or films a uniform light background is seen from the sample surrounded by the edge of the sealing ring. Gas bubbles, in the
10 optical path, scatter the light entering the cell and are imaged as dark areas,
Figure 3. Bubbles at the surface of the sample are sharply in focus and can be clearly seen down to very small sizes, typically 50 microns. Surface films produce varying levels of contrast and disrupt the uniformity of the image and so are also readily observed.

15

In a preferred embodiment of the invention the image from the *camera* [23] is transferred to a *computer* [25] controlling the ECV profiling measurement by the *cable* [24] and the image of the etched well is viewed in real time as the sample is etched.

20

In yet a further preferred embodiment of the invention the image is analysed by software that uses the result of the analysis to provide automatic feedback for elimination of gas bubbles and surface films.

25 In a preferred embodiment of the invention as illustrated in the present example the etched area can be measured by the same *camera* [23] and *lens* [22] as used for earlier observations. To enable this the *cell* [19] is retracted by the *mechanism* [20], to a position clear of the sample [19R] and the *supplementary lens* [21] is pivoted out of the beam path. The magnification of

the optics and the resolving power of the camera are such that the etched well area can be measured with sufficient resolution, typically better than 0.5%. Removing the supplementary lens [21] from the beam path gives a more stable optical configuration for accurate area determination. However, it is within the 5 scope of the invention to reverse the role of the correction lens, although this would not be preferred.

In a preferred embodiment of the invention as illustrated by the example the camera magnification is fixed and calibrated. The camera is interfaced to a 10 computer [25] and the image digitized. The data from the image is processed using software that can extract the etched well area, **Figure 4** and in the case of a 'blue film slice' or other suitable sample is able to differentiate between the wetted and illuminated areas, measure them and determine the excess area.

15 In the alternative arrangement the camera magnification could be variable and controllable via the software.

In a further alternative arrangement the supplementary lens [21] could be dispensed with and the *sample holder* [18] and *sample* [17] are translated 20 along the optical axis to bring the sample into focus on the camera.

In a further embodiment, illustrated in **Figure 5**, a *pivoting mirror* [26] is swung in front of the *imaging lens* [10]. This allows a *secondary light source* 25 [27] to illuminate the *sample* [17]. The secondary light source can be used to illuminate the sample with light of energy less than the samples band-gap, so that the sample can be viewed during electrical measurements such as capacitance-voltage measurements. By making the light source variable in wavelength it can be used to perform other optical/electrical measurements

such as reflection spectroscopy, photovoltage spectroscopy, photocurrent spectroscopy and modulated photovoltage spectroscopy.

By using light of energy less than the samples band-gap, samples containing a
5 pn junction can be viewed during etching of the p-type layer without etching
into the n-type layer where the conditions for the electrical measurements may
be different.

In yet a further embodiment, Figure 6 a *fold mirror* [30] replaces the *non-*
10 *reflective surface* [24]. This mirror reflects light from the *beamsplitter* [11] to
a *lens* [31], which focuses the light on to a *photo-detector* [32] for the purpose
of monitoring the light intensity.

CLAIMS

1. An in-situ method for improving the accuracy and repeatability of
5 Electrochemical Capacitance Voltage (ECV) profiling comprising the
steps of:

Providing a sample, a means of defining a measurement region on the
sample, an electrochemical cell to contain the electrolyte which is in
contact with the sample and ECV profiling in conventional manner;
10 monitoring the sample during the electrolyte fill cycle to observe and
obtain measurements of the presence of gas bubbles formed thereon;
monitoring the etched well during profiling;
measuring the etched well area at the end of the profile;
applying the said measurements to the raw profiling data to produce
15 adjusted data more reproducibly representative of the ECV profile.
2. A method in accordance with claim 1 wherein a suitable optical system
is used which can be combined with the ECV profiling apparatus to
both monitor the etched well during the measurement and accurately
20 measure the well area once the measurement is complete, without
removing the sample from the apparatus.
3. A method in accordance with claim 1 or claim 2 wherein the steps of
observation and measurement of the etched well comprise the use of a
25 light source of above band-gap energy, to illuminate the sample, and
the use if image collection means to collect a reflected light image from
the sample and image analysis means to analyse the reflected light
image from the sample and obtain the said measurements from the
etched well.

4. A method in accordance with claim 3 wherein the image collection means comprises digital imaging means and/or incorporates means to digitise the image for subsequent analysis by the image analyser.
5. A method in accordance with claim 3 or claim 4 wherein the reflected light image is directed towards the imaging means by use of suitable directing means such as a beam splitter.
- 10 6. A method in accordance with one of claims 3 to 5 wherein the same light source and imaging means are used to view and monitor the cell during the electrolyte fill cycle and the etched well area subsequently, in that the method comprises using the light source to generate a reflected light image of the cell during the electrolyte fill cycle and collecting the image via the imaging means, draining the electrochemical cell, taking the cell out of the optic path, using the light source to generate a reflected light image of the etched well area, and collecting the image via the imaging means to measure the said area.
- 15 7. An apparatus for improving the accuracy and repeatability of Electrochemical Capacitance Voltage (ECV) profiling comprises means to monitor a sample during the electrolyte fill cycle to observe and obtain measurements of the presence of gas bubbles and surface films formed thereon, means to monitor the etched well during profiling, means to obtain a measurement of the etched well area at the end of the profile, whereby the said measurements may be applied to raw profiling data to produce adjusted data more reproducibly representative of the ECV profile.

8. Apparatus in accordance with claim 7 wherein a suitable optical system is provided to obtain the said measurements.
9. Apparatus in accordance with claim 8 wherein a single optical system is provided, adapted for use in combination with the ECV profiling apparatus to both monitor the etched well during the measurement and accurately measure the well area once the measurement is complete, without removing the sample from the apparatus.
10. Apparatus in accordance with claim 9 wherein the means to monitor a sample during the electrolyte fill cycle, the means to monitor the etched well during profiling, and the means to obtain a measurement of the etched well comprises a single optical system including a light source of above band-gap energy to illuminate the sample, image collection means to collect a reflected light image from the sample and image analysis means to analyse the reflected light image from the sample and obtain the said measurements.
11. Apparatus in accordance with any one of claims 7 to 10 wherein the light source is a quartz halogen light source.
12. Apparatus in accordance with any one of claims 7 to 11 wherein the image collection means comprises digital imaging means and/or incorporates means to digitise the image for subsequent analysis by the image analyser.
13. Apparatus in accordance with claim 12 wherein the imaging means comprises a CCD camera.

14. Apparatus in accordance with any one of claims 7 to 13 wherein the analysing means comprise a suitable computer programmed with suitable analysis software.
- 5 15. Apparatus in accordance with claim 14 wherein the imaging means is interfaced to the computer to pass a digitized image thereto for processing the said measurements and/or applying the measurements to raw profiling data in the manner of the invention using suitable analysis software.
- 10 16. Apparatus in accordance with claim 14 or 15 wherein the software is adapted to process the data from the image so as to extract the etched well area and in the case of a 'blue film slice' is able to differentiate between the wetted and illuminated areas, measure them and determine 15 the excess area.
17. Apparatus in accordance with one of claims 14 to 16 wherein the image is processed using software to analyse the image and use the results of the analysis to provide automatic feedback for elimination of gas 20 bubbles and surface films.
18. Apparatus in accordance with one of claims 7 to 17 further comprising a beam splitter to direct the reflected light image towards the imaging means.
- 25 19. Apparatus in accordance with one of claims 7 to 18 further including means to receive an electrochemical cell in the optical path of the imaging means during the electrolyte fill cycle, which are adapted to enable the cell to be removed from the optical path subsequently, so the

same light source may be used to generate a reflected light image of the etched well area collecting the image via the imaging means to measure the said area.

- 5 20. Apparatus in accordance with one of claims 7 to 19 further comprising focussing means to compensate for the difference in focal length when the cell windows and electrolyte are in the path.
- 10 21. Apparatus in accordance with claim 20 wherein a fixed focus imaging means is provided, and a removable lens in the light path to the imaging means is provided to compensate for the difference in focal length.
- 15 22. Apparatus in accordance with one of claims 7 to 21 further comprising focussing means to focus the reflective image of the sample.
- 20 23. Apparatus in accordance with claim 22 comprising fixed focus imaging means, and wherein a mechanism is provided for moving the sample along the optical axis so that it focuses on the fixed focus imaging means.
- 25 24. Apparatus in accordance with one of claims 7 to 23 wherein the electrochemical cell is provided with a window for viewing and illuminating the sample, which is preferably slightly angled to prevent reflection from the surfaces of the window degrading the reflected image on the imaging means.
25. Apparatus in accordance with one of claims 7 to 24 further comprising a flip lens before the imaging means to correct for refraction by the

electrolyte and cell window when the apparatus is being used to view and/or monitor gas bubbles and surface films.

ABSTRACT

An apparatus and method for improving the accuracy of Electrochemical
5 Capacitance Voltage (ECV) profiling measurements by alerting the operator to
the presence of surface films or gas bubbles during the etching process and by
using this in-situ monitoring apparatus to determine the true measurement area
at the end of the measurement cycle and using the new value to recalculate the
data. By making the area measurement integral to the ECV tool, every sample
10 measurement can be corrected for the true measurement area, leading to
improved accuracy and eliminating a large source of error.

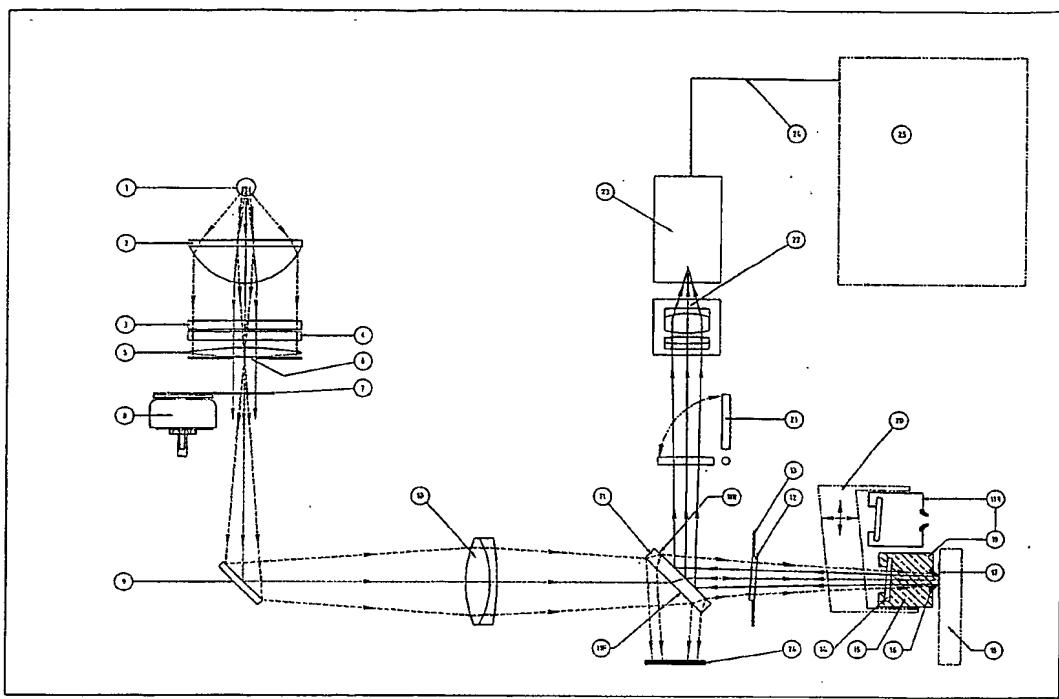


Figure 1.

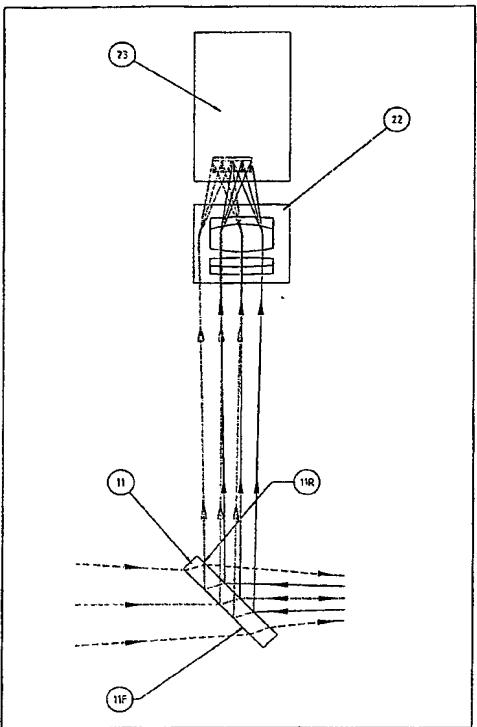


Figure 2.

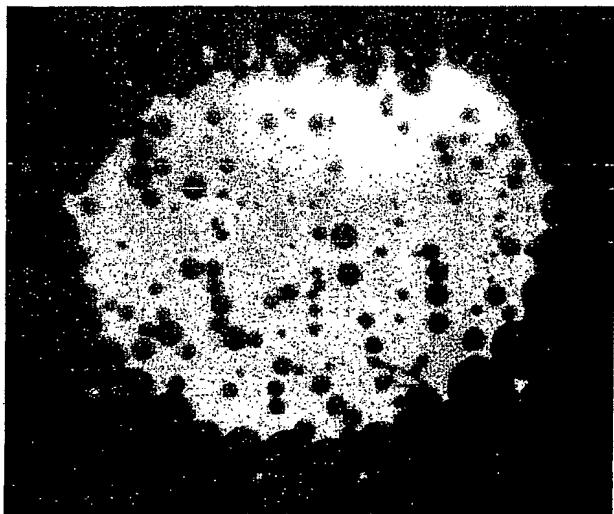


Figure 3.

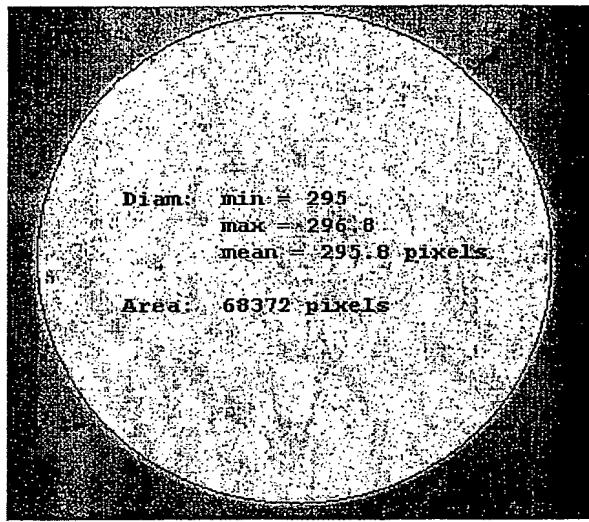


Figure 4.

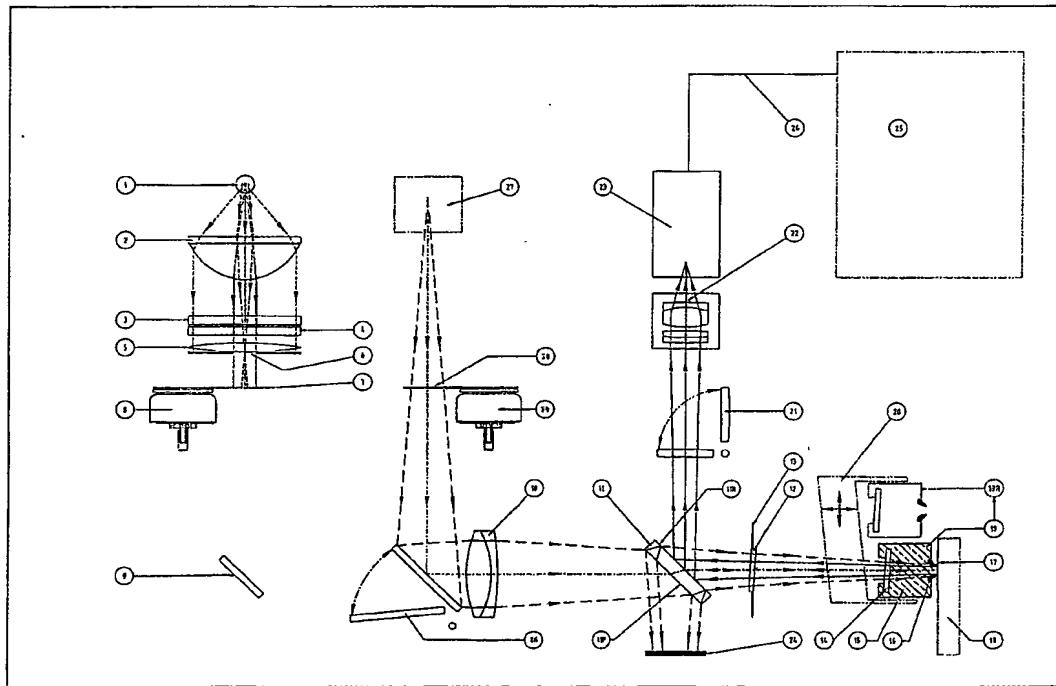


Figure 5.

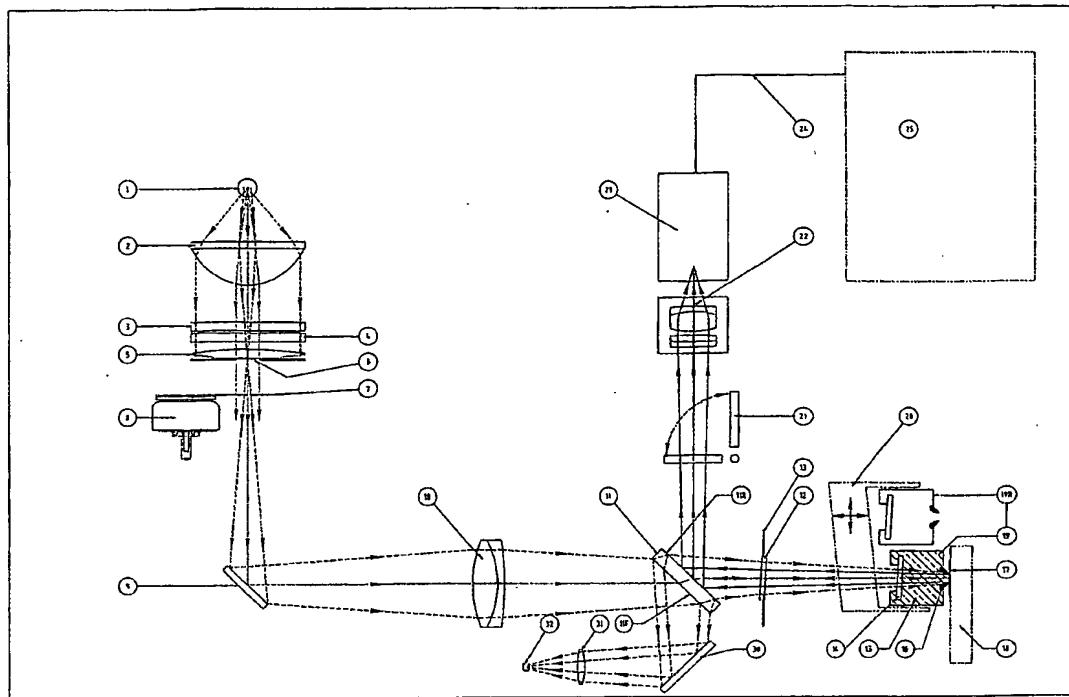


Figure 6.

**This Page is Inserted by IFW Indexing and Scanning
Operations and is not part of the Official Record.**

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images include but are not limited to the items checked:

- BLACK BORDERS**
- IMAGE CUT OFF AT TOP, BOTTOM OR SIDES**
- FADED TEXT OR DRAWING**
- BLURRED OR ILLEGIBLE TEXT OR DRAWING**
- SKEWED/SLANTED IMAGES**
- COLOR OR BLACK AND WHITE PHOTOGRAPHS**
- GRAY SCALE DOCUMENTS**
- LINES OR MARKS ON ORIGINAL DOCUMENT**
- REFERENCE(S) OR EXHIBIT(S) SUBMITTED ARE POOR QUALITY**
- OTHER:** _____

IMAGES ARE BEST AVAILABLE COPY.

As rescanning these documents will not correct the image problems checked, please do not report these problems to the IFW Image Problem Mailbox.